SD107WS

Schottky Barrier Diode

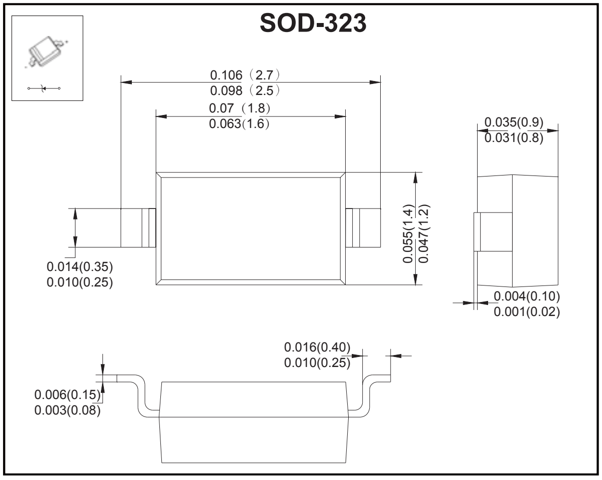
VOLTAGE RANGE: 30V PEAK PULSE POWER:250mW

FEATURES

- Low Forward Voltage Drop
- Guard Ring Die Construction for Transient
- Protection Ideal for Low Logic Level Applications
- Low Capacitance
- Also Available in Lead Free Version

MECHANICAL DATA

- Case: SOD-323 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 ℃ ambient temperature unless otherwise specified

Parameter	Symbol	Limit	Unit
Non-repetitive peak reverse voltage	V_{RM}	30	V
Forward current	I_{FM}	100	mA
Non-repetitive Peak Forward Surge Current @t = 8 .3ms	I_{FSM}	2	A
Powerdissipation T C=25℃	P_{tot}	250	mW
Thermal resistance junction to ambient	$T_{\theta JA}$	400	℃/W
Junction temperature	T_J	125	℃
Storage temperature	T_{STG}	-55~+150	℃

Electrical Specification (TA=25°C unless otherwise specified)

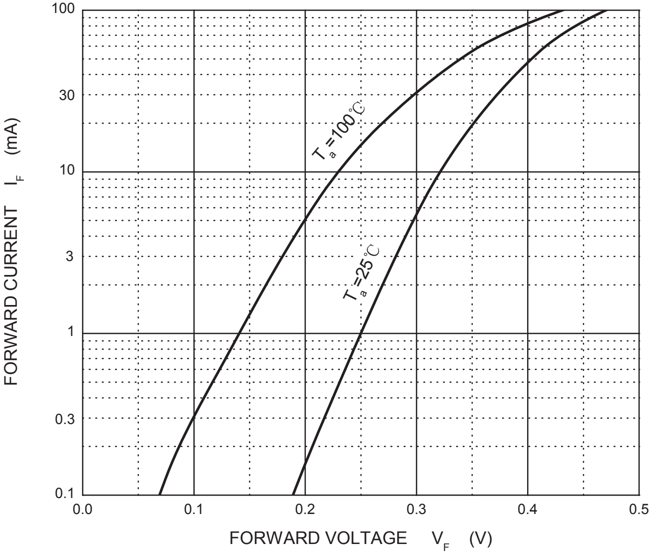
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	V_R	30			V	IR=100µA
Forward voltage	V_F		300		mV	I_F=2mA
			360			I_F=15mA
			430	550		I_F=50mA
			500	800		I_F=100mA
Reverse current	I_R			1	µA	V_R=25V
Capacitance between terminals	C_T		7		pF	V_R=10V,f=1MHz

MARKING: SG

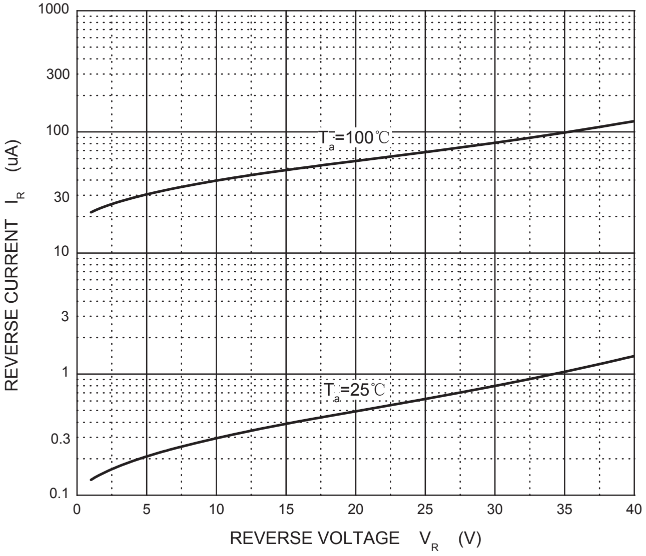
RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

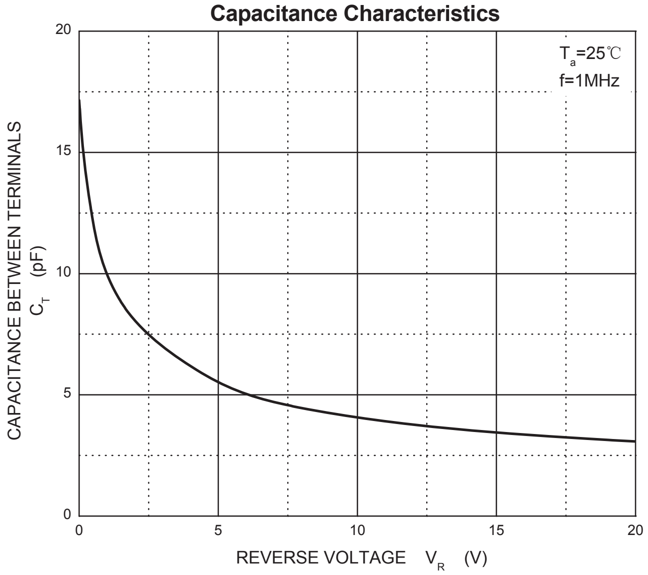
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve